Electronic Supplementary Material (ESI) for RSC Advances.

Electronic Supplementary Information

Luminescence properties and site occupancy of Ce^{3+} in Ba_2SiO_4: a combined experimental and ab initio study

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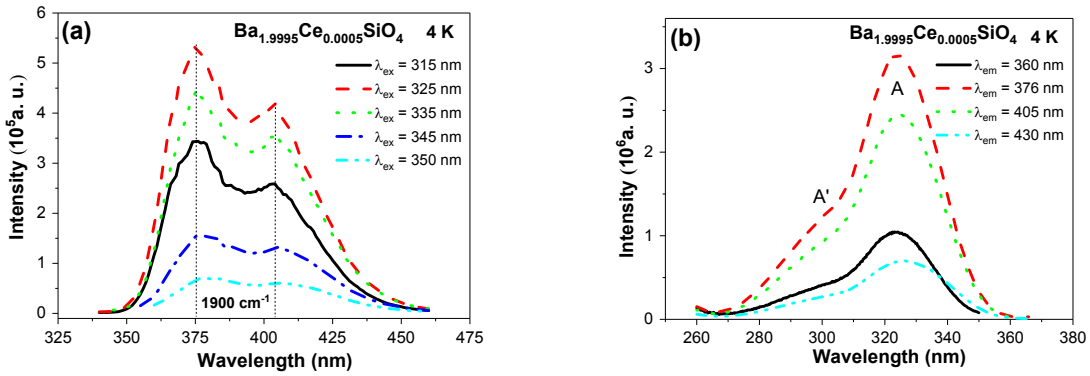

Fig. S1 (a) The UV-vis emission (λ_{ex} = 315, 325, 335, 345, and 350 nm) and (b) UV excitation spectra (λ_{em} = 360, 376, 405, and 430 nm) of $Ba_{1.9995}Ce_{0.0005}SiO_4$ at 4 K.

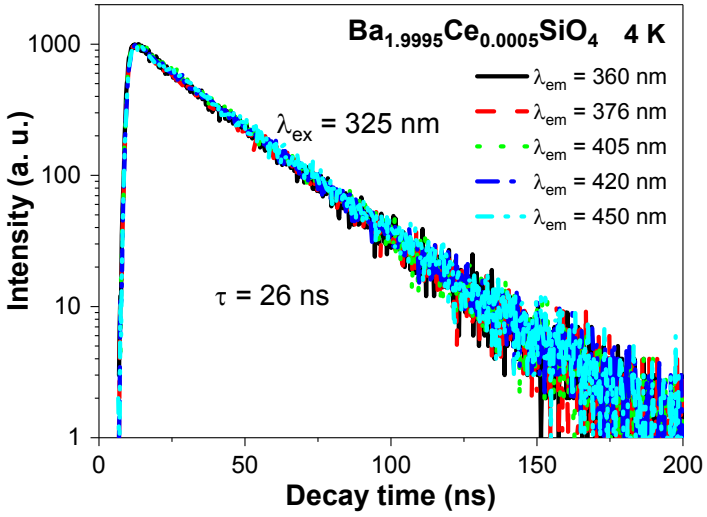

Fig. S2 Luminescence decay curves (λ_{ex} = 325 nm; λ_{em} = 360, 375, 405, 420, and 450 nm) of $Ba_{1.9995}Ce_{0.0005}SiO_4$ at 4 K.